

Reply under 37 CFR 1.116
Expedited Procedure
Technology Center 2800

AMENDMENTS TO THE CLAIMS

The following listing of claims replaces all prior versions, and listings, of claims in the application:

Claims 1-10 (Canceled)

11. (Original) A field effect transistor (FET) configured to sense a property of a medium, the FET comprising:

a source contact;

a drain contact;

a gate contact, wherein the gate contact defines a gate area disposed below and adjacent the gate contact; and

a sensing layer for sensing the property, wherein the sensing layer is disposed below the gate contact and wherein the sensing layer is exposed to the medium in the gate area.

12. (Original) The FET of claim 11, wherein the gate contact includes at least one perforation.

13. (Original) The FET of claim 11, further comprising a dielectric layer disposed between the gate contact and the sensing layer.

14. (Original) The FET of claim 13, wherein the dielectric layer includes at least one perforation in the gate area.

**Reply under 37 CFR 1.116
Expedited Procedure
Technology Center 2800**

15. (Original) The FET of claim 11, wherein the sensing layer comprises a dielectric layer.

Claims 16-20 (Canceled)